OSRAM V205Q121A-940 **Datasheet**





BIDOS® P2433 Q

V205Q121A-940

940 nm Multi-Mode VCSEL Power Array Designed for Sensor Field of Interest: 60° x 45°





Applications

- 3D Sensing
- Access Control & Security

- Eye, face and hand tracking

Features

- Package: QFN Package
- ESD: 2 kV acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2)
- Very small SMT package
- VCSEL power array
- High optical power
- IR Laser with photodiode



Ordering Information

 $I_{_{\rm F}}$ = 4 A; $t_{_{\rm D}}$ = 300 μ s; D = 0.05 ; $T_{_{\rm A}}$ = 25 °C

Optical output power Ordering Code Type

typ.

V205Q121A-940 6.5 W Q65113A2192

Depending on the mode of operation, these devices emit highly concentrated visible and non-visible light which can be hazardous to the human eye. Products which incorporate these devices must follow the safety precautions given in the "Notes" section.



Maximum Ratings

T_A = 25 °C

| Parameter | Symbol | | Values |
|--|----------------------|------|-------------------|
| Operating temperature | Top | min. | -20 °C |
| (refers to T _A ; T _A = 85°C with reduced efficiency) | · | max. | 85 °C |
| Storage temperature | T _{stg} | min. | -40 °C |
| | | max. | 100 °C |
| Soldering temperature | Ts | max. | 260 °C |
| $t_{\text{max}} = 10 \text{ s}$ | | | |
| ESD withstand voltage | V _{ESD} | max. | 2 kV |
| acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2) | | | |
| IR Laser | | | |
| Junction temperature | Tj | max. | 125 °C |
| Forward current pulsed | I _{F pulse} | max. | 4 A |
| $t_p \le 600 \ \mu s; \ D = 0.01$ | | | |
| Reverse voltage 5) | V_{R} | max. | Not designed for |
| | | | reverse operation |
| Photodiode | | | |
| Reverse voltage 5) | V_R | max. | 20 V |

Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device.



Characteristics

 t_p = 300 µs; D = 0.05; T_A = 25 °C

| Parameter | Symbol | | Values | |
|--|------------------------|------|------------|--|
| IR Laser | | | | |
| Peak wavelength 6) | λ_{peak} | min. | 931 nm | |
| | | typ. | 940 nm | |
| | | max. | 949 nm | |
| Optical output power 7) | P _{opt} | min. | 5.0 W | |
| $I_F = 4 A$ | | typ. | 6.5 W | |
| Field of view (HFOV) | ΘΙΙ | typ. | 66 ° | |
| Angle at E _e ,50% level, normalized to the centroid | | | | |
| Field of view (VFOV) | Θ_{\perp} | typ. | 53 ° | |
| Angle at E _e ,50% level, normalized to the centroid | | | | |
| Dimensions of chip area | LxW | typ. | 0.9 x 1.0 | |
| | | | mm x mm | |
| Slope efficiency | η | min. | 1.50 W/ A | |
| I _F = 1 A 2 A | | typ. | 1.75 W/ A | |
| Power conversion efficiency | η _{tot} | typ. | 45 % | |
| I _F = 4 A | | | | |
| Threshold current | I _{th} | typ. | 0.5 A | |
| | | max. | 0.9 A | |
| Forward voltage 8) | V _F | min. | 3.0 V | |
| I _F = 4 A | | typ. | 3.7 V | |
| | | max. | 4.5 V | |
| Rise time | t _r | typ. | 1 ns | |
| 10% and 90% of le max | | | | |
| Fall time | t _f | typ. | 1 ns | |
| 10% and 90% of le max | | | | |
| Temperature coefficient of wavelength | TCλ | typ. | 0.07 nm/ K | |
| Thermal resistance junction solder point real | R _{thJS} real | max. | 11 K/ W | |
| $t_p = 0.01 \text{ s}$ | | | | |



Characteristics

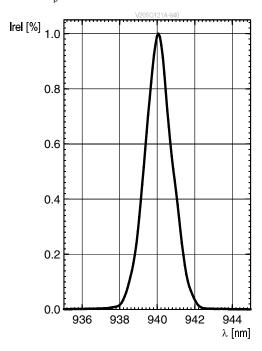
T_A = 25 °C

| Parameter | Symbol | | Values |
|--|--------------------|--------------|------------------------|
| Photodiode | | | |
| Wavelength of max sensitivity | λ _{S max} | typ. | 840 nm |
| Spectral range of sensitivity | λ10% | typ. | 400 1100 nm |
| Photocurrent $\lambda = 940 \text{ nm}, E_e = 0.5 \text{ mW/cm}^2, V_R = 3.3 \text{ V}$ | lР | typ. | 0.188 μΑ |
| Photocurrent with VCSEL @I _F = 4 A, V _R = 3.3 V | l _Р | typ. | 850 μΑ |
| Dimensions of chip area | LxW | typ. | 0.38 x 0.38 mm x mm |
| Forward voltage I _F = 10 mA, E = 0 | V _F | typ. max. | 0.85 V 1.00 V |
| Capacitance E _e = 0 mW/cm², f = 1 MHz, V _R = 0V | C ₀ | typ. | 1.3 pF |
| Dark current VR = 3.3 V | l _R | typ. max. | 0.1 nA 30 nA |
| Open-circuit voltage λ = 940 nm, E _e = 0.5 mW/cm ² | Vo | typ. | 260 mV |
| Short-circuit current $\lambda = 940 \text{ nm}, E_e = 0.5 \text{ mW/cm}^2, V_R = 0 \text{ V}$ | Isc | typ. | 188 nA |
| Rise time λ = 940 nm, V_R = 0.7 V, R_L = 50 Ω | tr | typ. | 205 ns |
| Fall time λ = 940 nm, V_R = 0.7 V, R_L = 50 Ω | t _f | typ. | 215 ns |
| Temperature coefficient of sensitivity λ = 940 nm, E _e = 0.5 mW/cm ² , V _R = 3.3V | TCı | typ. | 0.23 %/ K |



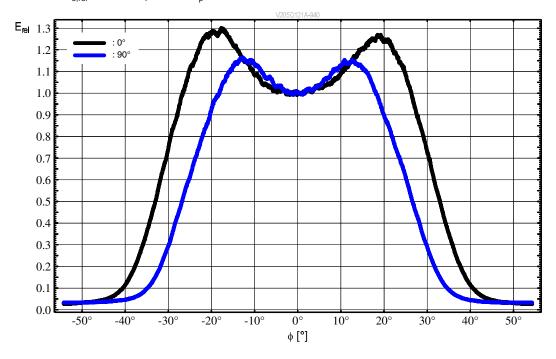
Relative Spectral Emission 1), 2)

• infrared (940 nm): $I_{\rm e,rel}$ = f (λ); $I_{\rm F}$ = 4000 mA; $t_{\rm p}$ = 300 μs



Radiation Characteristics 1), 2)

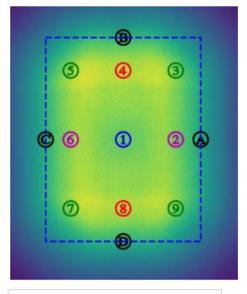
• infrared (940 nm): $E_{e,rel} = f(\phi)$; $I_F = 4$ A; $t_p = 300 \ \mu s$; D = 0.05





Far-Field Illumination Pattern 2)

• infrared (940 nm): $I_{rel} = f(\phi)$; $I_F = 4$ A; $t_p = 300 \ \mu s$; D = 0.05



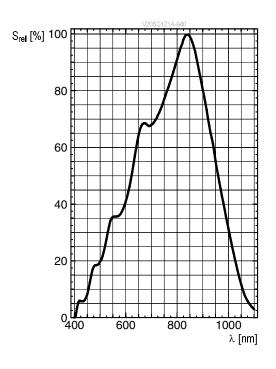
| Sensor FOI 60°(H) x 45°(V) (dotted | line) |
|------------------------------------|-------|
|------------------------------------|-------|

| | Min | Тур | Max |
|---|------|------|------|
| 1 | 100% | 100% | 100% |
| 2 | 90% | 110% | 130% |
| 3 | 90% | 110% | 130% |
| 4 | 100% | 123% | 145% |
| 5 | 90% | 110% | 130% |
| 6 | 90% | 110% | 130% |
| 7 | 90% | 110% | 130% |
| 8 | 100% | 123% | 145% |
| 9 | 90% | 110% | 130% |
| Α | 65% | 85% | 105% |
| В | 65% | 85% | 105% |
| С | 65% | 85% | 105% |
| D | 65% | 85% | 105% |



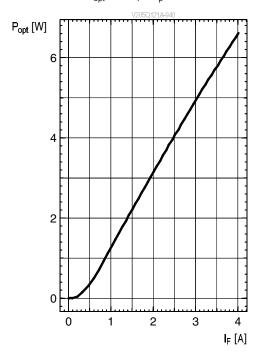
Relative Spectral Sensitivity 1), 2)

■ photodiode: $S_{rel} = f(\lambda)$; $V_R = 3.3 \text{ V}$



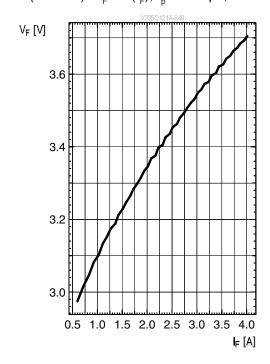
Optical Output Power 1), 2)

• infrared (940 nm): $P_{opt} = f(I_F)$; $t_p = 300 \ \mu s$; D = 0.05



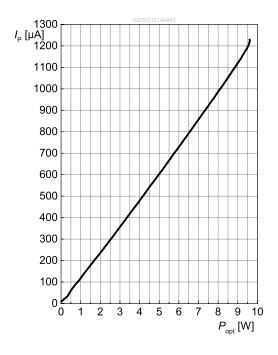
Forward Voltage 1), 2)

• infrared (940 nm): $V_F = f(I_F)$; $t_p = 300 \ \mu s$; D = 0.05



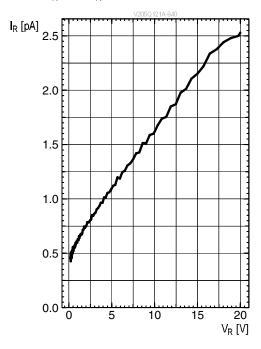
Photocurrent 1), 2)

■ photodiode: $I_P = f(P_{opt})$



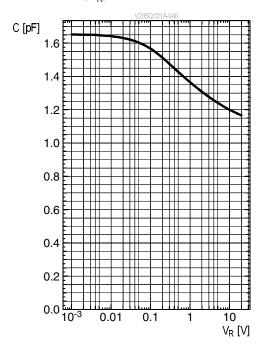
Dark Current 1), 2)

■ photodiode: $I_R = f(V_R)$



Capacitance 1), 2)

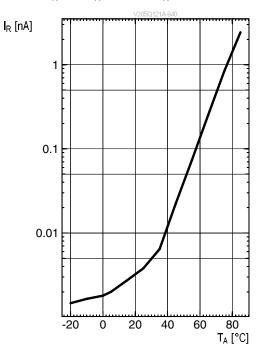
■ photodiode: $C = f(V_R)$; E = 0





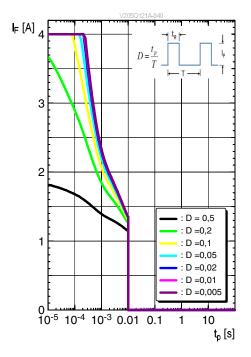
Dark Current 1)

■ photodiode: $I_R = f(T_A)$; E = 0; $V_R = 3.3 \text{ V}$



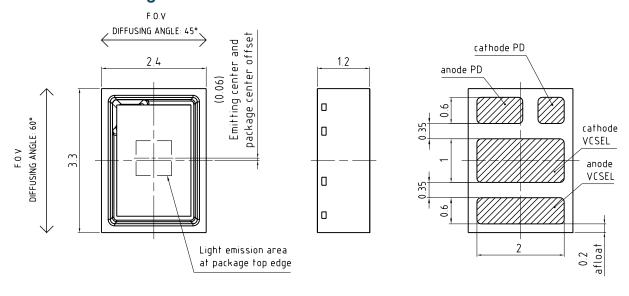
Permissible Pulse Handling Capability

• infrared (940 nm): $I_F = f(t_p)$; D = param.; $T_S = 85$ °C; (not characterized for DC condition)





Dimensional Drawing 3)



general tolerance ± 0.1 lead finish Au

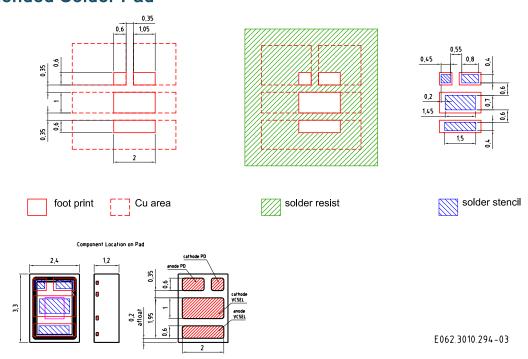
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Further Information:

Approximate Weight: 20.0 mg



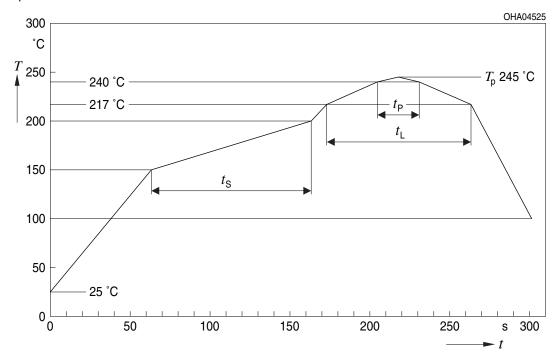
Recommended Solder Pad 3)





Reflow Soldering Profile

Product complies to MSL Level 3 acc. to JEDEC J-STD-020E



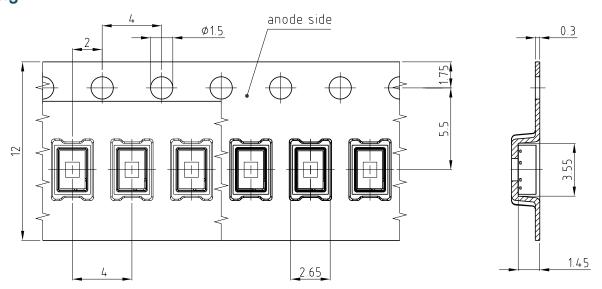
| Profile Feature | Symbol | ymbol Pb-Free (SnAgCu) Assembly | | | Unit |
|---|--------------------------------|---------------------------------|----------------|---------|------|
| | | Minimum | Recommendation | Maximum | |
| Ramp-up rate to preheat*) | | | 2 | 3 | K/s |
| 25 °C to 150 °C | | | | | |
| Time t _s | t_s | 60 | 100 | 120 | S |
| T_{Smin} to T_{Smax} | | | | | |
| Ramp-up rate to peak*) | | | 2 | 3 | K/s |
| T_{Smax} to T_{P} | | | | | |
| Liquidus temperature | T_{L} | | 217 | | °C |
| Time above liquidus temperature | $t_{\scriptscriptstyle \perp}$ | | 80 | 100 | S |
| Peak temperature | T _P | | 245 | 260 | °C |
| Time within 5 °C of the specified peak temperature T _P - 5 K | t _P | 10 | 20 | 30 | S |
| Ramp-down rate* T _p to 100 °C | | | 3 | 6 | K/s |
| Time 25 °C to T _P | | | | 480 | S |

All temperatures refer to the center of the package, measured on the top of the component

^{*} slope calculation DT/Dt: Dt max. 5 s; fulfillment for the whole T-range



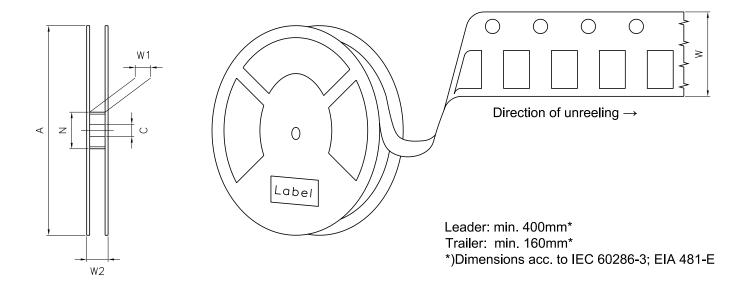
Taping 3)



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Tape and Reel 4)

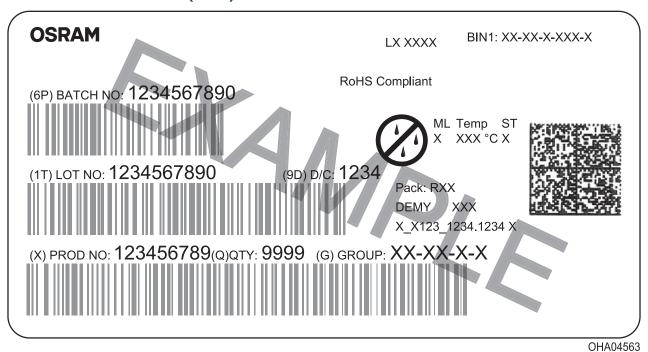


Reel Dimensions

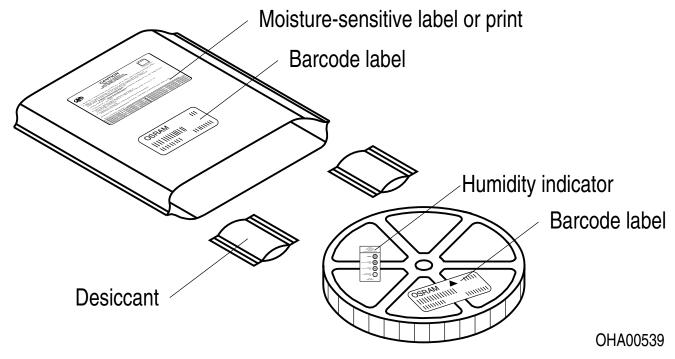
| Α | W | N_{\min} | W_1 | $W_{2 \text{max}}$ | Pieces per PU |
|--------|---------------------|------------|-------------|---------------------|---------------|
| 180 mm | 12 + 0.3 / - 0.1 mm | 60 mm | 12.4 + 2 mm | 18.4 mm | 2000 |



Barcode-Product-Label (BPL)



Dry Packing Process and Materials





Notes

Depending on the mode of operation, these devices emit highly concentrated visible and non visible light which can be hazardous to the human eye. Products which incorporate these devices have to follow the safety precautions given in IEC 60825-1.

Subcomponents of this device contain, in addition to other substances, metal filled materials including silver. Metal filled materials can be affected by environments that contain traces of aggressive substances. Therefore, we recommend that customers minimize device exposure to aggressive substances during storage, production, and use. Devices that showed visible discoloration when tested using the described tests above did show no performance deviations within failure limits during the stated test duration. Respective failure limits are described in the IEC60810.

For further application related information please visit https://ams-osram.com/support/application-notes



Disclaimer

Attention please!

The information describes the type of component and shall not be considered as assured characteristics. Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances.

For information on the types in question please contact our Sales Organization.

If printed or downloaded, please find the latest version on our website.

Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

Product and functional safety devices/applications or medical devices/applications

Our components are not developed, constructed or tested for the application as safety relevant component or for the application in medical devices.

Our products are not qualified at module and system level for such application.

In case buyer – or customer supplied by buyer – considers using our components in product safety devices/ applications or medical devices/applications, buyer and/or customer has to inform our local sales partner immediately and we and buyer and /or customer will analyze and coordinate the customer-specific request between us and buyer and/or customer.



Glossary

- 1) Typical Values: Due to the special conditions of the manufacturing processes of semiconductor devices, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.
- 2) **Testing temperature:** T_A = 25°C (unless otherwise specified)
- 3) Tolerance of Measure: Unless otherwise noted in drawing, tolerances are specified with ±0.1 and dimensions are specified in mm.
- 4) Tape and Reel: All dimensions and tolerances are specified acc. IEC 60286-3 and specified in mm.
- 5) **Reverse Operation:** This product is intended to be operated applying a forward current within the specified range. Applying any continuous reverse bias or forward bias below the voltage range of light emission shall be avoided because it may cause migration which can change the electro-optical characteristics or damage the LED.
- 6) Wavelength: The wavelengths are measured with a tolerance of ±1 nm.
- 7) Brightness: The brightness values are measured with a tolerance of ±11%.
- 8) Forward Voltage: The forward voltages are measured with a tolerance of ±0.1 V.



| Revis | ion | History | , |
|-------|-----|----------------|---|
|-------|-----|----------------|---|

| Version | Date | Change |
|---------|------------|---|
| 1.0 | 2021-10-01 | Initial Version |
| 1.1 | 2023-05-04 | Applications Maximum Ratings New Layout Characteristics |
| 1.2 | 2024-06-26 | Recommended Solder Pad Taping |



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